

2PD601ART 50 V, 100 mA NPN general-purpose transistor Rev. 01 — 15 March 2007

Product data sheet

Product profile 1.

1.1 General description

NPN general-purpose transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

PNP complement: 2PB709ART.

1.2 Features

- General-purpose transistor
- Small SMD plastic package

1.3 Applications

General-purpose switching and amplification

1.4 Quick reference data

Table 1. Quick reference data Symbol Conditions Parameter Min Тур Max Unit V_{CEO} collector-emitter voltage open base --50 V I_{C} collector current 100 mΑ -h_{FF} DC current gain $V_{CE} = 10 V;$ 210 -340 $I_C = 2 \text{ mA}$

Pinning information 2.

Pin	Description	Simplified outline	Symbol
1	base		
2	emitter		3
3	collector		



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3. Ordering information

Table 3. Ordering information				
Type number	Package			
	Name	Description	Version	
2PD601ART	-	plastic surface-mounted package; 3 leads	SOT23	

4. Marking

Table 4.Marking codes

Type number	Marking code ^[1]
2PD601ART	C3*

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

5. Limiting values

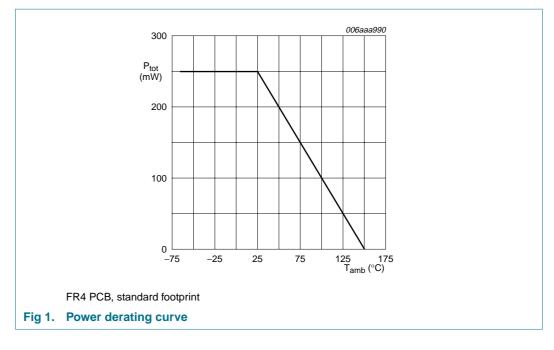
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		0,	,		
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter	-	60	V
V_{CEO}	collector-emitter voltage	open base	-	50	V
V_{EBO}	emitter-base voltage	open collector	-	6	V
I _C	collector current		-	100	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	200	mA
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms	-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> _	250	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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6. Thermal characteristics

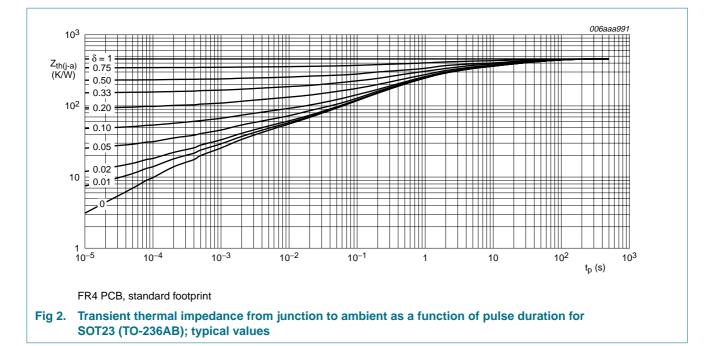
Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	500	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	140	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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7. Characteristics

Table 7. Characteristics

 $T_{amb} = 25 \circ C$ unless otherwise specified.

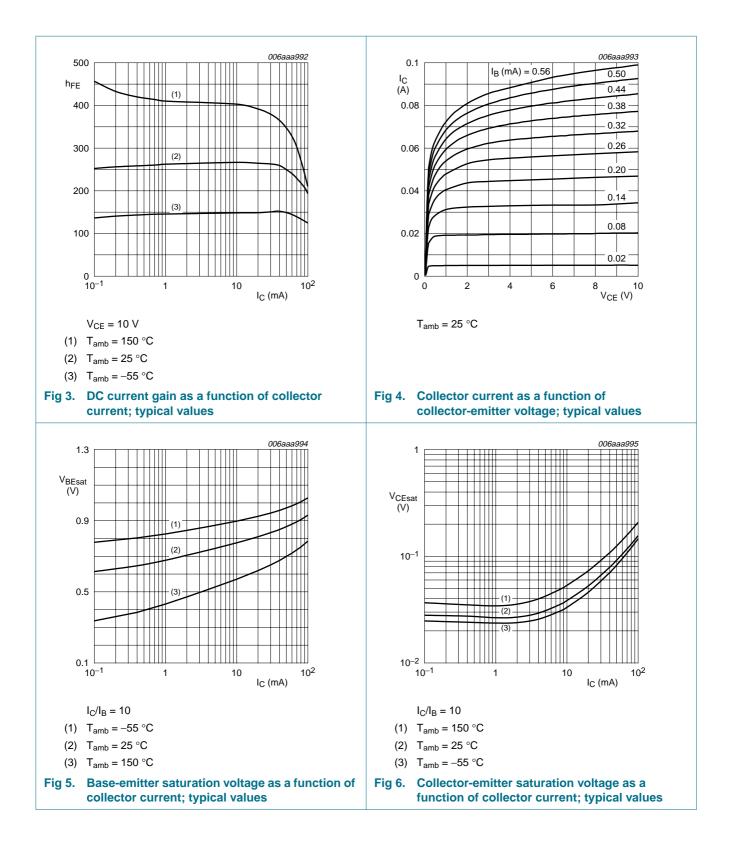
1 amb - 20	*C unless otherwise spec	cined:				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	$V_{CB} = 60 \text{ V}; I_E = 0 \text{ A}$	-	-	10	nA
	current	$V_{CB} = 60 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 ^{\circ}\text{C}$	-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 V; I_C = 0 A$	-	-	10	nA
h _{FE}	DC current gain	V _{CE} = 2 V; I _C = 100 mA	90	-	-	
		$V_{CE} = 10 \text{ V};$ $I_C = 2 \text{ mA}$	210	-	340	
V _{CEsat}	collector-emitter saturation voltage	I _C = 100 mA; I _B = 10 mA	<u>[1]</u> _	-	250	mV
f _T	transition frequency	V _{CE} = 10 V; I _C = 2 mA; f = 100 MHz	100	-	-	MHz
C _c	collector capacitance	$\label{eq:VCB} \begin{split} V_{CB} &= 10 \text{ V};\\ I_E &= i_e = 0 \text{ A};\\ f &= 1 \text{ MHz} \end{split}$	-	-	3	pF

[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02$.

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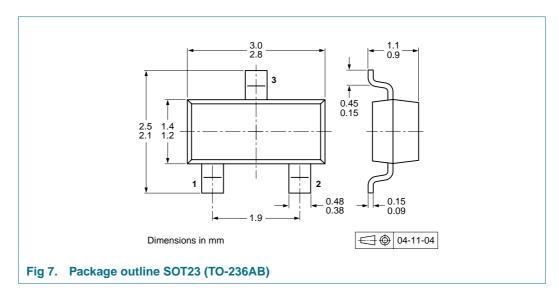
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8. Package outline



9. Packing information

Table 8. Packing methods

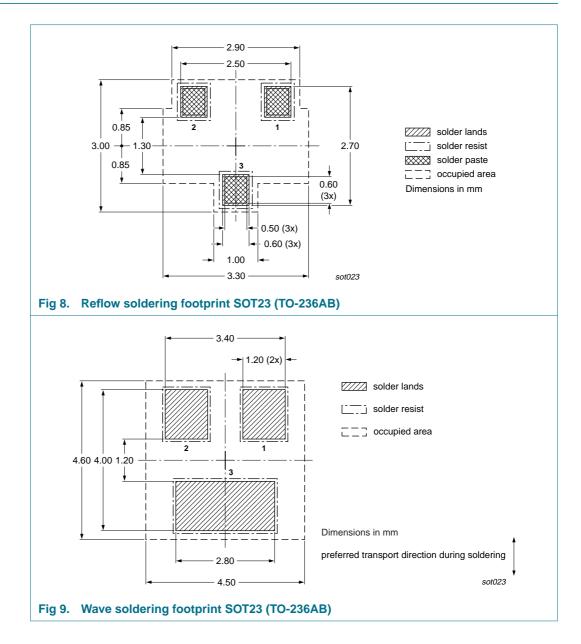
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing	Packing quantity	
			3000	10000	
2PD601ART	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235	

[1] For further information and the availability of packing methods, see Section 13.

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10. Soldering



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11. Revision history

Table 9. Revision	Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes	
2PD601ART_1	20070315	Product data sheet	-	-	

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12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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